

Appl. No.: 10/79,101
Amdt. Dated July 26, 2005
Reply to Office Action Dated April 26, 2005

Amendments to the Specification:

Please replace the paragraph on page 4 with the following amended paragraph:

The present invention achieves technical advantages as an electrically programmable transistor fuse having a source and drain disposed in a semiconductor substrate and further having a double-gate arrangement disposed in a single layer of polysilicon in which one gate is capacitively couple coupled to the drain region. The transistor further includes a coupling device adapted to increase the capacitive coupling of the one gate and the drain region for enabling reduction in fuse programming voltage, wherein programming of the transistor fuse is effectuated via application of a voltage signal to the drain in which the voltage signal is less than the junction breakdown of the transistor fuse.

On page 5, after the paragraph that begins "Figure 1A illustrates," please insert the following paragraph to describe Figure 1B:

Figure 1B shows operating bias for a conventional structure of Figure 1.